**Product data sheet** 

### 1. General description

Planar passivated sensitive gate four quadrant triac in a SOT78 plastic package intended for use in general purpose bidirectional switching and phase control applications. This sensitive gate "series E" triac is intended to be interfaced directly to microcontrollers, logic integrated circuits and other low power gate trigger circuits.

#### 2. Features and benefits

- Direct triggering from low power drivers and logic ICs
- High blocking voltage capability
- Low holding current for low current loads and lowest EMI at commutation
- Planar passivated for voltage ruggedness and reliability
- Sensitive gate
- Triggering in all four quadrants

### 3. Applications

- General purpose motor control
- General purpose switching

#### 4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$V_{DRM}$	repetitive peak off- state voltage		-	-	600	V
I <sub>TSM</sub>	non-repetitive peak on- state current	full sine wave; $T_{j(init)} = 25 \text{ °C}$ ; $t_p = 20 \text{ ms}$ ; Fig. 4; Fig. 5		-	65	Α
I <sub>T(RMS)</sub>	RMS on-state current	full sine wave; T <sub>mb</sub> ≤ 102 °C; <u>Fig. 1;</u> <u>Fig. 2; Fig. 3</u>	TRO	N	8   C	А
Static chara	acteristics					
I <sub>GT</sub>	gate trigger current	$V_D = 12 \text{ V; } I_T = 0.1 \text{ A; } T2 + G+;$ $T_j = 25 \text{ °C; } Fig. 7$	-	2.5	10	mA
		$V_D = 12 \text{ V; } I_T = 0.1 \text{ A; } T2 + \text{ G-;}$ $T_j = 25 \text{ °C; } Fig. 7$	-	4	10	mA
		$V_D = 12 \text{ V; } I_T = 0.1 \text{ A; } T2-\text{ G-;}$ $T_j = 25 \text{ °C; } Fig. 7$	-	5	10	mA





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Symbol	Parameter	Conditions	Min	Тур	Max	Unit
		$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; \text{ T2- G+};$ $T_j = 25 \text{ °C}; \frac{\text{Fig. 7}}{\text{Fig. 7}}$	-	11	25	mA
I <sub>H</sub>	holding current	V <sub>D</sub> = 12 V; T <sub>j</sub> = 25 °C; <u>Fig. 9</u>	-	2.5	20	mA

### 5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	T1	main terminal 1	mb	T2—T1
2	T2	main terminal 2	705	sym051
3	G	gate		· ·
mb	Т2	mounting base; main terminal 2		
			TO-220AB (SOT <mark>78)</mark>	

# 6. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	rsion
BT137-600E	TO-220AB	plastic single-ended package; heatsink mounted; 1 mounting hole; 3-lead TO-220AB	)T78
BT137-600E/DG	TO-220AB	plastic single-ended package; heatsink mounted; 1 mounting hole; 3-lead TO-220AB	)T78
BT137-600E/L01	TO-220AB	plastic single-ended package; heatsink mounted; 1 mounting hole; 3-lead TO-220AB	OT78

# 7. Marking

Table 4. Marking codes

Type number	Marking code
BT137-600E	
BT137-600E/DG	BT137-600E/DG
BT137-600E/L01	

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### 8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
$V_{DRM}$	repetitive peak off-state voltage			-	600	V
I <sub>T(RMS)</sub>	RMS on-state current	full sine wave; $T_{mb} \le 102 \text{ °C}$ ; Fig. 1; Fig. 2; Fig. 3		_	8	A
I <sub>TSM</sub>	non-repetitive peak on-state current	full sine wave; $T_{j(init)} = 25 ^{\circ}C;$ $t_p = 20 \text{ms};  \underline{Fig. 4};  \underline{Fig. 5}$		+	65	A
		full sine wave; $T_{j(init)} = 25 \text{ °C}$ ; $t_p = 16.7 \text{ ms}$		_	71	A
l <sup>2</sup> t	I <sup>2</sup> t for fusing	t <sub>p</sub> = 10 ms; SIN		-	21	A <sup>2</sup> s
dl <sub>T</sub> /dt	rate of rise of on-state current	$I_T$ = 12 A; $I_G$ = 0.2 A; $dI_G/dt$ = 0.2 A/ $\mu$ s; T2+ G+		-	50	A/µs
		$I_T$ = 12 A; $I_G$ = 0.2 A; $dI_G/dt$ = 0.2 A/µs; T2+ G-		-	50	A/µs
		$I_T = 12 \text{ A}$ ; $I_G = 0.2 \text{ A}$ ; $dI_G/dt = 0.2 \text{ A}/\mu\text{s}$ ; T2- G-	7	-	50	A/µs
		$I_T$ = 12 A; $I_G$ = 0.2 A; $dI_G/dt$ = 0.2 A/µs; T2- G+		-	10	A/µs
I <sub>GM</sub>	peak gate current			-	2	Α
P <sub>GM</sub>	peak gate power			-	5	W
P <sub>G(AV)</sub>	average gate power	over any 20 ms period		-	0.5	W
T <sub>stg</sub>	storage temperature			-40	150	°C
Tj	junction temperature			-	125	°C



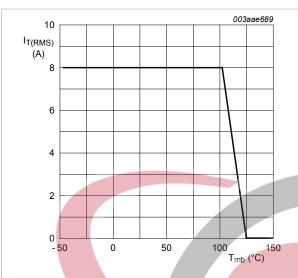


Fig. 1. RMS on-state current as a function of mounting base temperature; maximum values

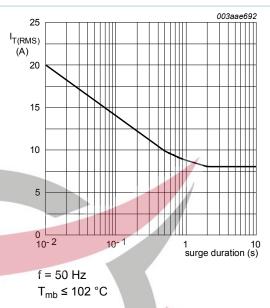
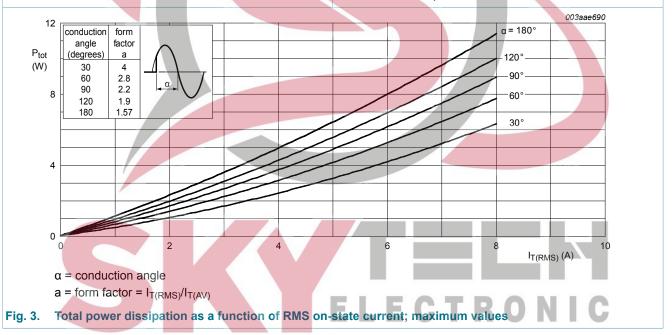
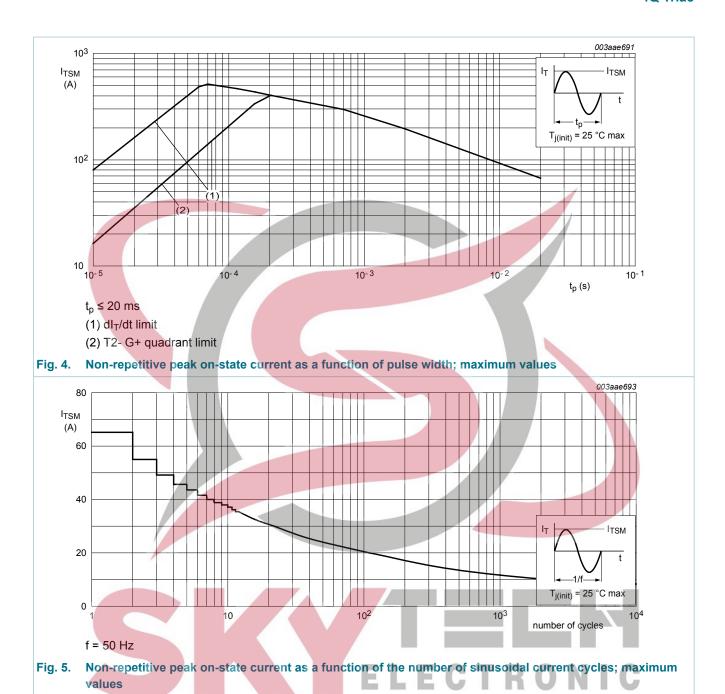


Fig. 2. RMS on-state current as a function of surge duration; maximum values



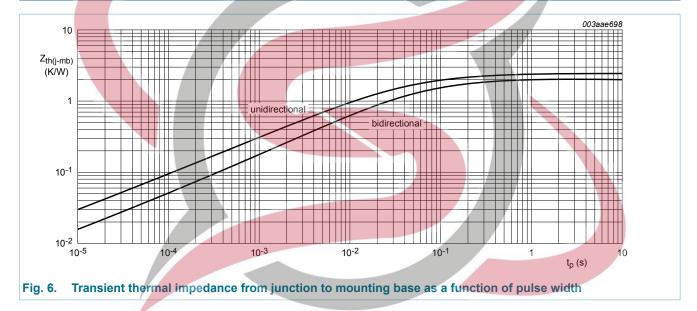


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### 9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R <sub>th(j-mb)</sub>	thermal resistance	half cycle; Fig. 6	-	-	2.4	K/W
	from junction to mounting base	full cycle; Fig. 6	-	-	2	K/W
R <sub>th(j-a)</sub>	thermal resistance from junction to ambient	in free air	-	60	-	K/W



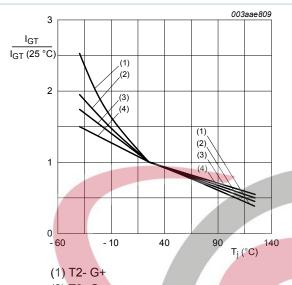


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### 10. Characteristics

Table 7. Characteristics

	Characteristics		1.			
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static char	racteristics					_
I <sub>GT</sub>	gate trigger current	$V_D = 12 \text{ V; } I_T = 0.1 \text{ A; } T2 + G+;$ $T_j = 25 \text{ °C; } \frac{\text{Fig. 7}}{}$	-	2.5	10	mA
		$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; T2+ \text{ G-};$ $T_j = 25 \text{ °C}; Fig. 7$	-	4	10	mA
		$V_D = 12 \text{ V; } I_T = 0.1 \text{ A; } T2-\text{ G-;}$ $T_j = 25 \text{ °C; } Fig. 7$		5	10	mA
		$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; \text{ T2- G+};$ $T_j = 25 \text{ °C}; Fig. 7$		11	25	mA
lL	latching current	$V_D = 12 \text{ V; } I_G = 0.1 \text{ A; } T2+ G+;$ $T_j = 25 \text{ °C; } Fig. 8$	-	3	25	mA
		$V_D = 12 \text{ V}; I_G = 0.1 \text{ A}; T2+ G-;$ $T_j = 25 \text{ °C}; Fig. 8$	-	14	35	mA
		$V_D = 12 \text{ V}; I_G = 0.1 \text{ A}; \text{ T2- G-};$ $T_j = 25 \text{ °C}; \frac{\text{Fig. 8}}{}$	47	3	25	mA
		$V_D = 12 \text{ V; } I_G = 0.1 \text{ A; T2- G+;}$ $T_j = 25 \text{ °C; } \frac{\text{Fig. 8}}{\text{C}}$	-	4	35	mA
I <sub>H</sub>	holding current	V <sub>D</sub> = 12 V; T <sub>j</sub> = 25 °C; <u>Fig. 9</u>	-	2.5	20	mA
V <sub>T</sub>	on-state voltage	I <sub>T</sub> = 10 A; T <sub>j</sub> = 25 °C; <u>Fig. 10</u>	-	1.3	1.65	V
$V_{GT}$	gate trigger voltage	$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; T_j = 25 \text{ °C};$ Fig. 11	-	0.7	1	V
		$V_D = 400 \text{ V}; I_T = 0.1 \text{ A}; T_j = 125 \text{ °C};$ Fig. 11	0.25	0.4	-11	V
I <sub>D</sub>	off-state current	V <sub>D</sub> = 600 V; T <sub>j</sub> = 125 °C	-	0.1	0.5	mA
Dynamic c	haracteristics					
dV <sub>D</sub> /dt	rate of rise of off-state voltage	V <sub>DM</sub> = 402 V; T <sub>j</sub> = 125 °C; (V <sub>DM</sub> = 67% of V <sub>DRM</sub> ); exponential waveform; gate open circuit	RO	50	I-C	V/µs
t <sub>gt</sub>	gate-controlled turn-on time	$I_{TM}$ = 12 A; $V_D$ = 600 V; $I_G$ = 0.1 A; $dI_G/$ dt = 5 A/µs	-	2	-	μs



- (2) T2- G-
- (3) T2+ G-
- (4) T2+ G+

Fig. 7. Normalized gate trigger current as a function of junction temperature

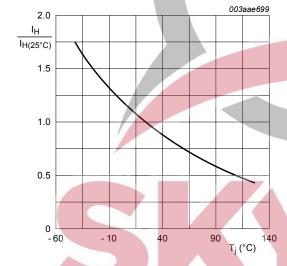


Fig. 9. Normalized holding current as a function of junction temperature

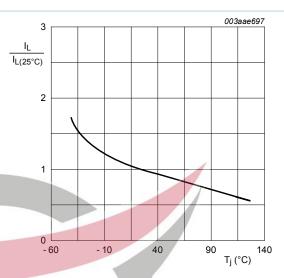
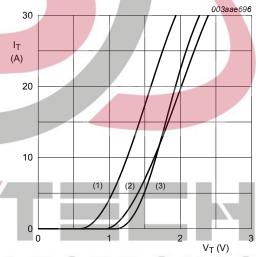


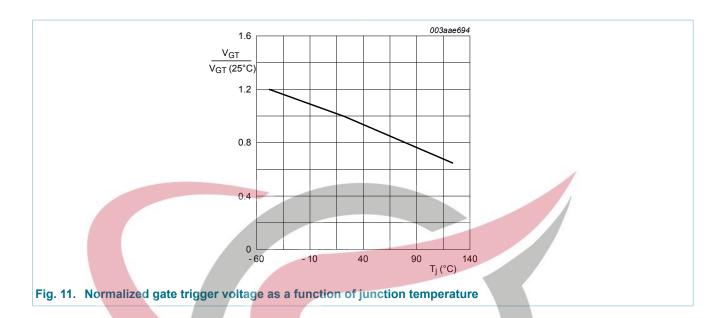
Fig. 8. Normalized latching current as a function of junction temperature





- (1) T<sub>i</sub> = 125 °C; typical values
- (2) T<sub>i</sub> = 125 °C; maximum values
- (3)  $T_j = 25$  °C; maximum values

Fig. 10. On-state current as a function of on-state voltage





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### 11. Package outline

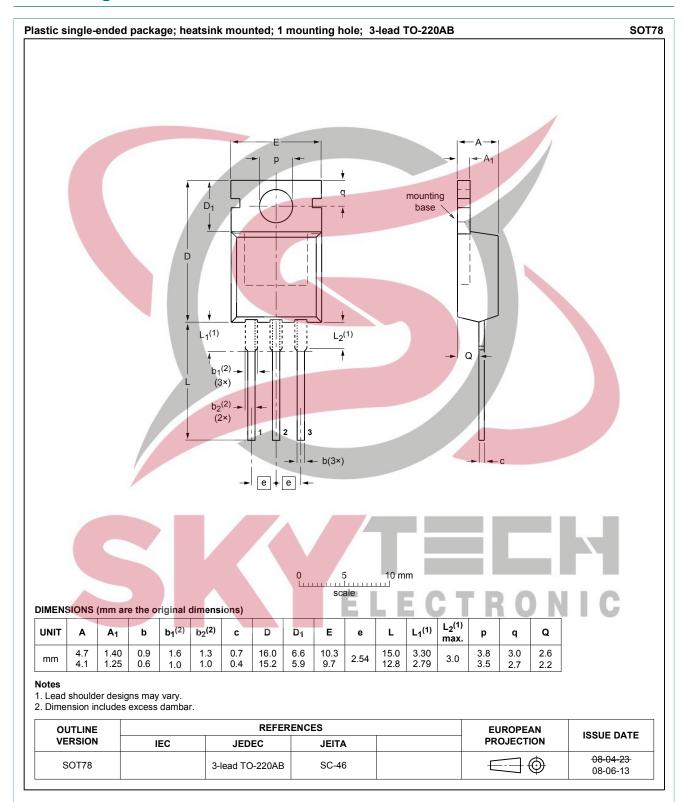


Fig. 12. Package outline TO-220AB (SOT78)

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#### 12. Legal information

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Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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